



DMP610DL

Product Summary

BV _{DSS}	Rds(on) Max	I D T _A = +25°C
-60V	10Ω @ V _{GS} = -5V	-180mA

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

P-CHANNEL ENHANCEMENT MODE MOSFET

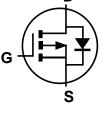
Mechanical Data

- Case: SOT23
- Case Material: UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish (Lead Free Plating).
- Solderable per MIL-STD-202, Method 208 3
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)



SOT23

Top View



Equivalent Circuit

D G S

Top View

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP610DL-7	SOT23	3,000/Tape & Reel
DMP610DL-13	SOT23	10,000/Tape & Reel

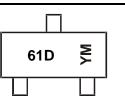
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

<1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



61D = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Notes:

Date Code Rey												
Year	2016		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	D		Н	-	J	K	L	М	N	0	Р	R
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	-60	V		
Gate-Source Voltage	Vgss	±30	V		
Continuous Drain Current (Note 6) $V_{GS} = -5V$ State $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$			ID	-180 -130	mA
Maximum Continuous Body Diode Forward Curre	nt (Note 6)	ls	-0.5	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1	IDM	-1.2	A		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	310	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	405	°C/W
Total Power Dissipation (Note 6)		PD	500	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	251	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

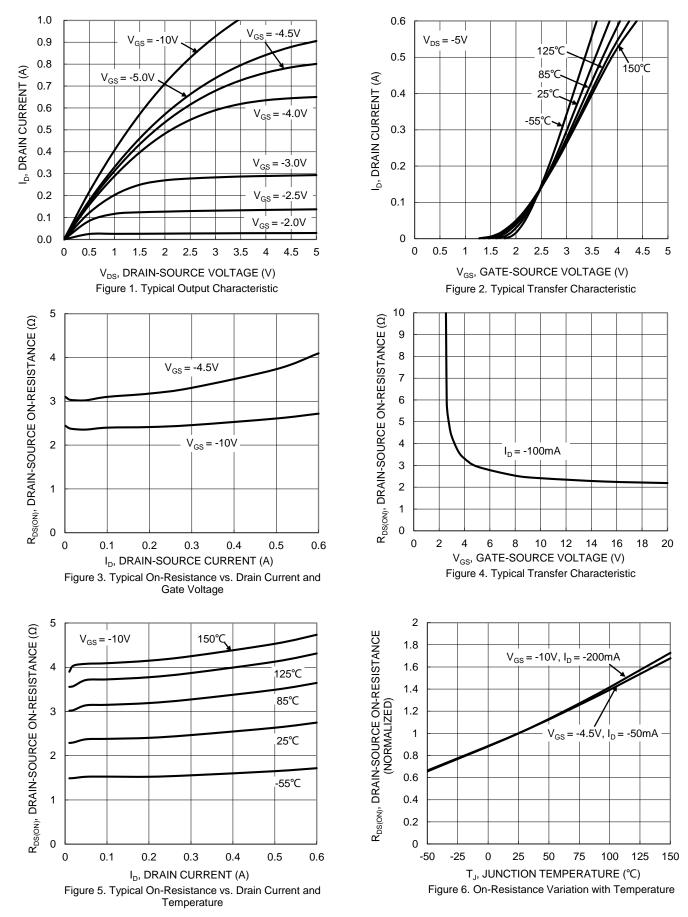
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						-
Drain-Source Breakdown Voltage	BV _{DSS}	-60	_		V	$V_{GS} = 0V, I_D = -250 \mu A$
Zero Gate Voltage Drain Current	IDSS	—	_	-1	μA	$V_{DS} = -60V, V_{GS} = 0V$
Gate-Source Leakage	lgss	—	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	VGS(TH)	-0.8	—	-2.0	V	$V_{DS} = V_{GS}, I_D = -1mA$
Static Drain-Source On-Resistance	R _{DS(ON)}	—	_	10	Ω	$V_{GS} = -5V, I_D = -0.1A$
Forward Transconductance	g fs	—	0.25	_	S	V _{DS} = -25V, I _D = -0.1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss		24.6		pF	
Output Capacitance	Coss	—	4.8		pF	V _{DS} = -25V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance	C _{RSS}	—	2.8		pF	
Gate Resistance	Rg		2,000	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1.0MHz$
Total Gate Charge (V _{GS} = -4.5V)	QG	—	280		рС	
Total Gate Charge (VGS = -10V)	QG	—	560		рС	Vps = -10V. lp = -100mA
Gate-Source Charge	Qgs	—	90	_	рС	VDS = -10V, 1D = -100MA
Gate-Drain Charge	Qgd	_	77	_	рС	
Turn-On Delay Time	tD(ON)	_	2.8		ns	
Turn-On Rise Time	t _R	_	2.6	_	ns	V _{DD} = -30V, I _D = -0.27A,
Turn-Off Delay Time	tD(OFF)		11.1	_	ns	$R_{GEN} = 50\Omega$, $V_{GS} = -10V$
Turn-Off Fall Time	tF		7.2		ns	

Notes:

Device mounted on FR-4 PCB, with minimum recommended pad layout.
 Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

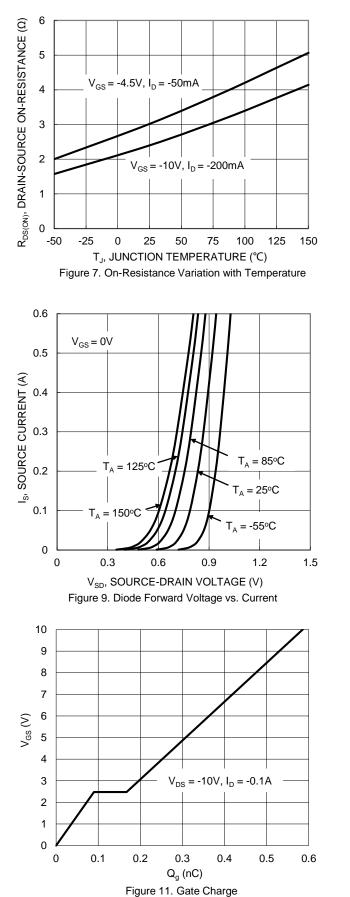


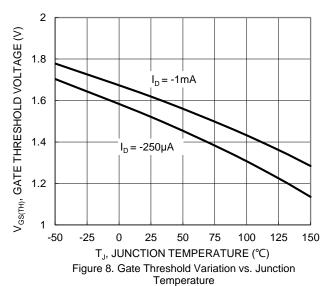
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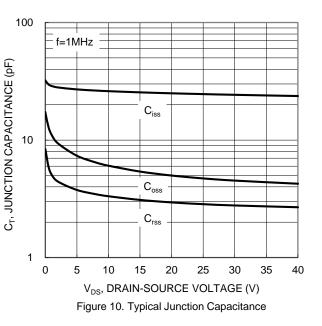




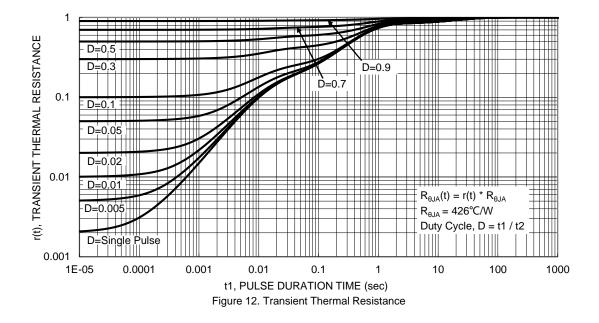
DMP610DL







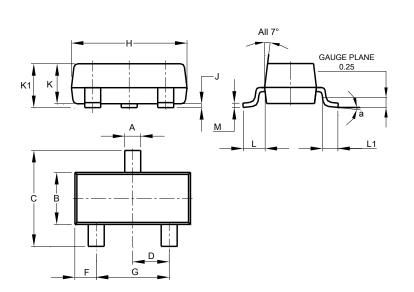






Package Outline Dimensions

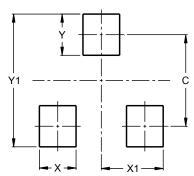
Please see http://www.diodes.com/package-outlines.html for the latest version.



	SOT23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
в	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
К	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	0°	8°						
All	All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9

SOT23

SOT23



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